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[International Rectifier \(Infineon Technologies Americas Corp.\)
IRF2807S](#)

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sales@integrated-circuit.com

International **IR** Rectifier

- Advanced Process Technology
- Ultra Low On-Resistance
- Dynamic dv/dt Rating
- 175°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated

Description

Advanced HEXFET® Power MOSFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications. The D²Pak is a surface mount power package capable of accommodating die sizes up to HEX-4. It provides the highest power capability and the lowest possible on-resistance in any existing surface mount package. The D²Pak is suitable for high current applications because of its low internal connection resistance and can dissipate up to 2.0W in a typical surface mount application.

The through-hole version (IRF2807L) is available for low-profile applications.

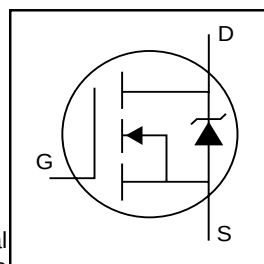
Absolute Maximum Ratings

	Parameter	Max.	Units
I_D @ $T_C = 25^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V	82⑦	A
I_D @ $T_C = 100^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V	58	
I_{DM}	Pulsed Drain Current ①	280	
P_D @ $T_C = 25^\circ\text{C}$	Power Dissipation	230	W
	Linear Derating Factor	1.5	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
I_{AR}	Avalanche Current①	43	A
E_{AR}	Repetitive Avalanche Energy①	23	mJ
dv/dt	Peak Diode Recovery dv/dt ③	5.9	V/ns
T_J	Operating Junction and	-55 to + 175	°C
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	
	Mounting torque, 6-32 or M3 screw	10 lbf•in (1.1N•m)	

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	0.65	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB mount)**	—	40	

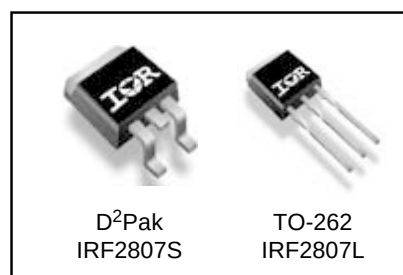
PD - 94170
IRF2807S
IRF2807L
HEXFET® Power MOSFET



$$V_{DSS} = 75V$$

$$R_{DS(on)} = 13m\Omega$$

$$I_D = 82A⑦$$



D²Pak
IRF2807S

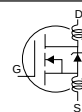
TO-262
IRF2807L

IRF2807S/IRF2807L

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Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	75	—	—	V	V _{GS} = 0V, I _D = 250μA
ΔV _{(BR)DSS} /ΔT _J	Breakdown Voltage Temp. Coefficient	—	0.074	—	V/°C	Reference to 25°C, I _D = 1mA
R _{DS(on)}	Static Drain-to-Source On-Resistance	—	—	13	mΩ	V _{GS} = 10V, I _D = 43A ④
V _{GS(th)}	Gate Threshold Voltage	2.0	—	4.0	V	V _{DS} = V _{GS} , I _D = 250μA
g _{fs}	Forward Transconductance	38	—	—	S	V _{DS} = 50V, I _D = 43A④
I _{DSS}	Drain-to-Source Leakage Current	—	—	25	μA	V _{DS} = 75V, V _{GS} = 0V
		—	—	250		V _{DS} = 60V, V _{GS} = 0V, T _J = 150°C
I _{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	V _{GS} = 20V
	Gate-to-Source Reverse Leakage	—	—	-100		V _{GS} = -20V
Q _g	Total Gate Charge	—	—	160	nC	I _D = 43A
Q _{gs}	Gate-to-Source Charge	—	—	29		V _{DS} = 60V
Q _{gd}	Gate-to-Drain ("Miller") Charge	—	—	55		V _{GS} = 10V, See Fig. 6 and 13
t _{d(on)}	Turn-On Delay Time	—	13	—	ns	V _{DD} = 38V
t _r	Rise Time	—	64	—		I _D = 43A
t _{d(off)}	Turn-Off Delay Time	—	49	—		R _G = 2.5Ω
t _f	Fall Time	—	48	—		V _{GS} = 10V, See Fig. 10 ④
L _D	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact
L _S	Internal Source Inductance	—	7.5	—		
C _{iss}	Input Capacitance	—	3820	—	pF	V _{GS} = 0V
C _{oss}	Output Capacitance	—	610	—		V _{DS} = 25V
C _{rss}	Reverse Transfer Capacitance	—	130	—		f = 1.0MHz, See Fig. 5
E _{AS}	Single Pulse Avalanche Energy②	—	1280⑤	340⑥		I _{AS} = 50A, L = 370μH



Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I _S	Continuous Source Current (Body Diode)	—	—	82⑦	A	MOSFET symbol showing the integral reverse p-n junction diode.
I _{SM}	Pulsed Source Current (Body Diode)①	—	—	280		
V _{SD}	Diode Forward Voltage	—	—	1.2	V	T _J = 25°C, I _S = 43A, V _{GS} = 0V ④
t _{rr}	Reverse Recovery Time	—	100	150	ns	T _J = 25°C, I _F = 43A
Q _{rr}	Reverse Recovery Charge	—	410	610	nC	di/dt = 100A/μs ④
t _{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L _S +L _D)				

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
- ② Starting T_J = 25°C, L = 370μH
R_G = 25Ω, I_{AS} = 43A, V_{GS} = 10V (See Figure 12)
- ③ I_{SD} ≤ 43A, di/dt ≤ 300A/μs, V_{DD} ≤ V_{(BR)DSS},
T_J ≤ 175°C
- ④ Pulse width ≤ 400μs; duty cycle ≤ 2%.

⑤ This is a typical value at device destruction and represents operation outside rated limits.

⑥ This is a calculated value limited to T_J = 175°C.

⑦ Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 75A.

**When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994

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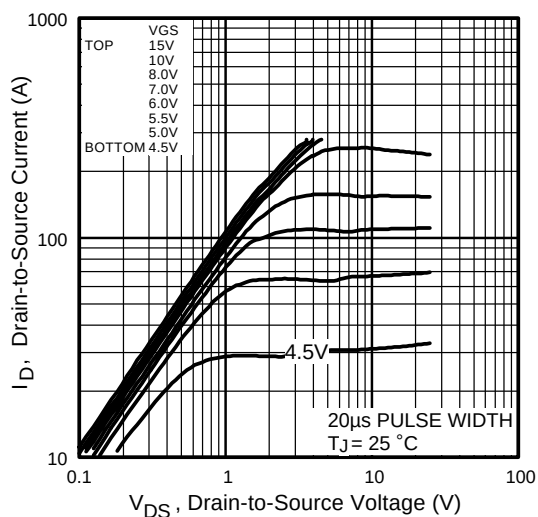


Fig 1. Typical Output Characteristics

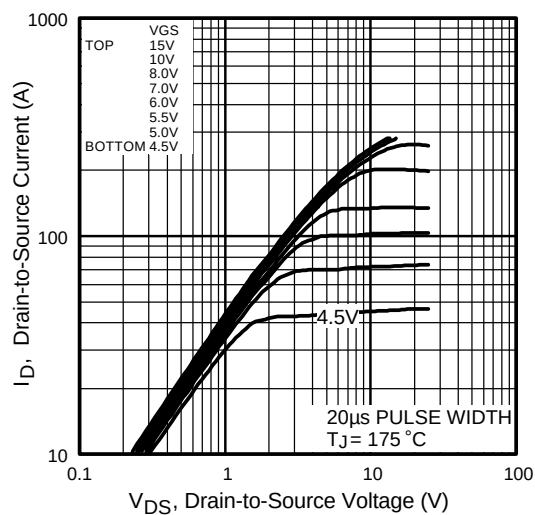


Fig 2. Typical Output Characteristics

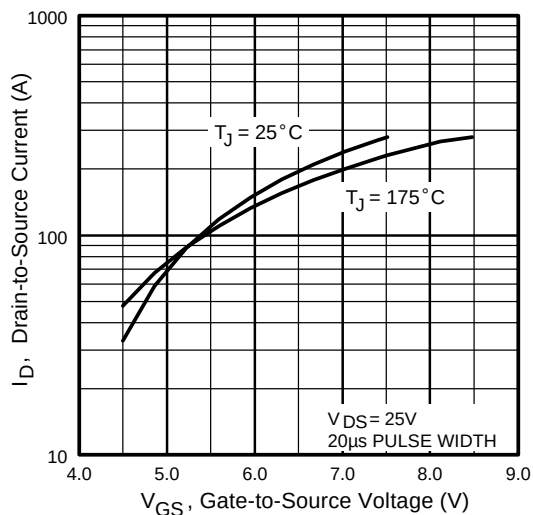


Fig 3. Typical Transfer Characteristics

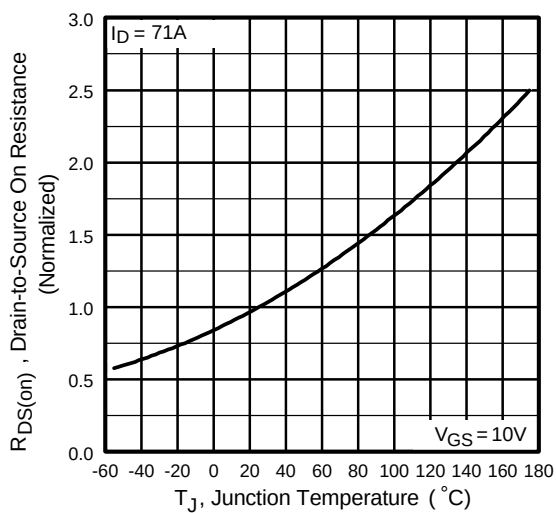


Fig 4. Normalized On-Resistance
Vs. Temperature

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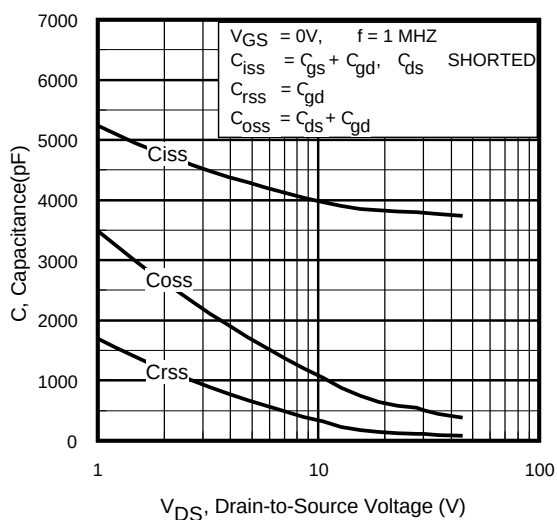


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

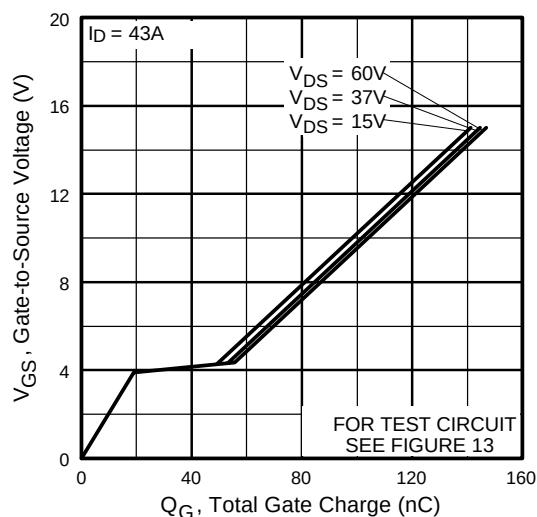


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

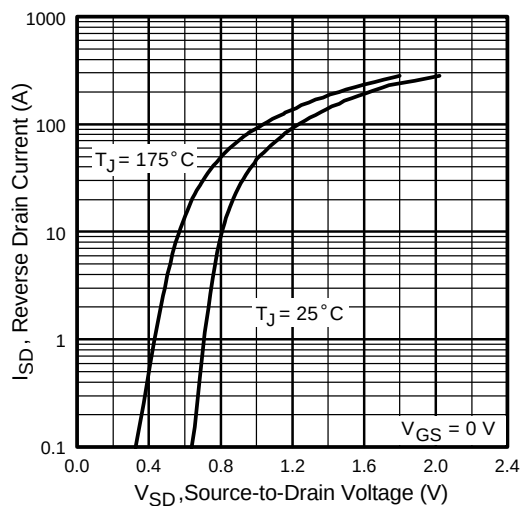


Fig 7. Typical Source-Drain Diode Forward Voltage

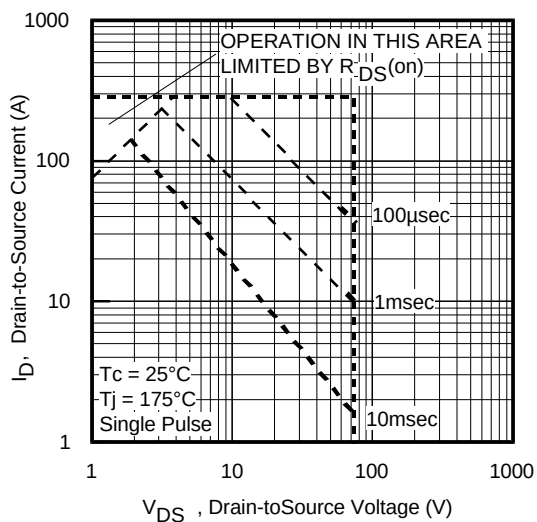


Fig 8. Maximum Safe Operating Area

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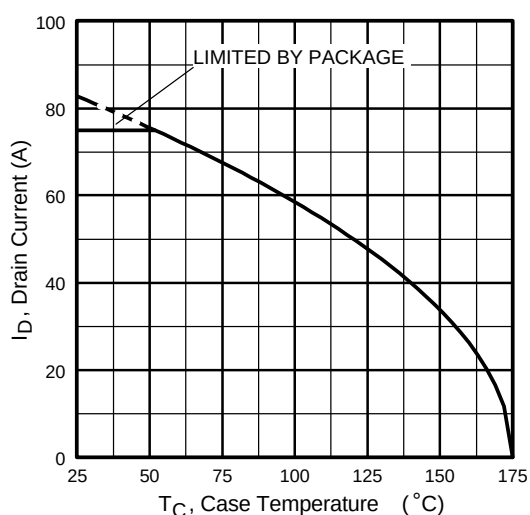


Fig 9. Maximum Drain Current Vs. Case Temperature

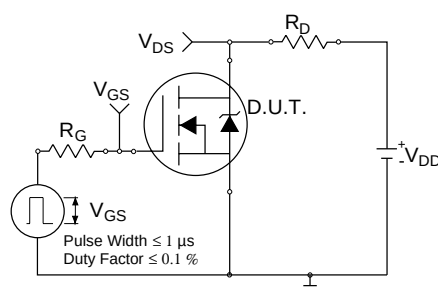


Fig 10a. Switching Time Test Circuit

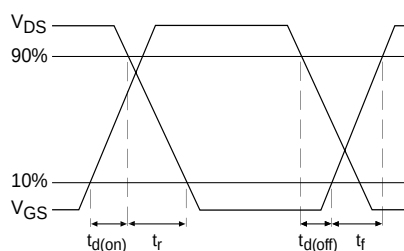


Fig 10b. Switching Time Waveforms

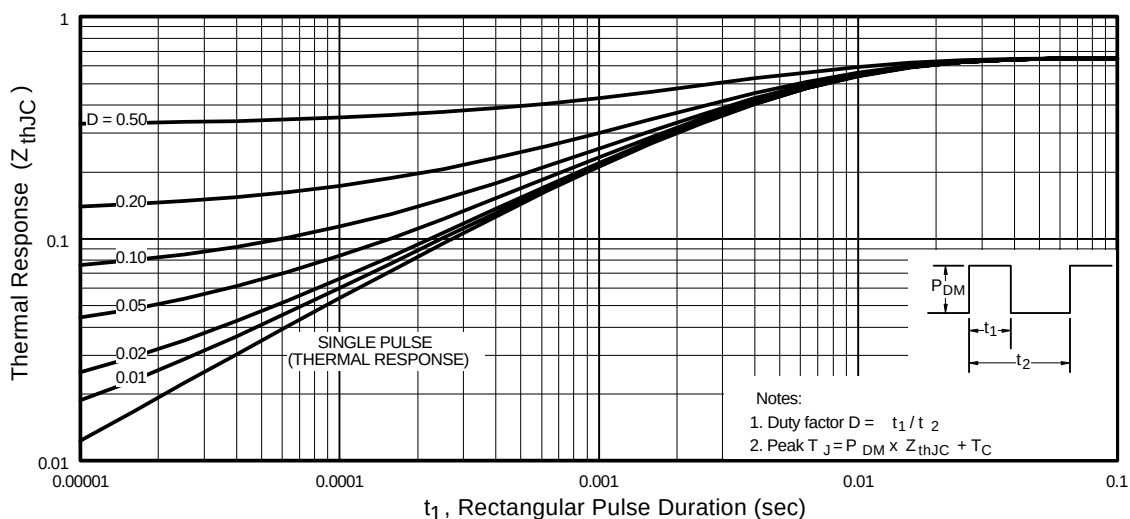


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

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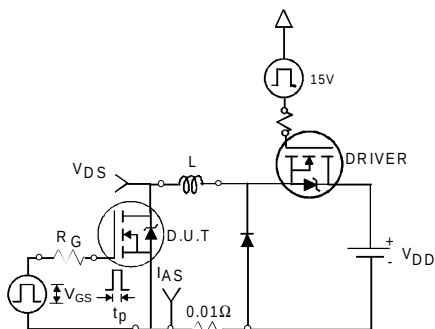


Fig 12a. Unclamped Inductive Test Circuit

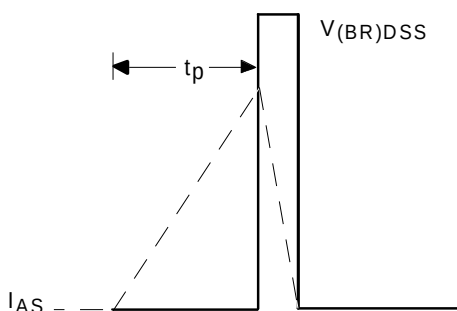


Fig 12b. Unclamped Inductive Waveforms

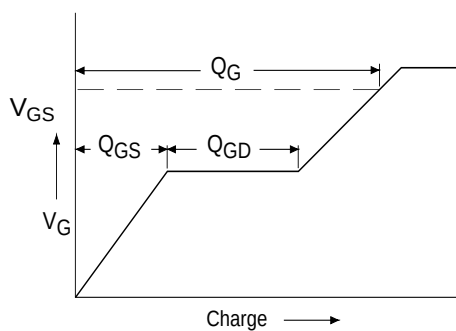


Fig 13a. Basic Gate Charge Waveform

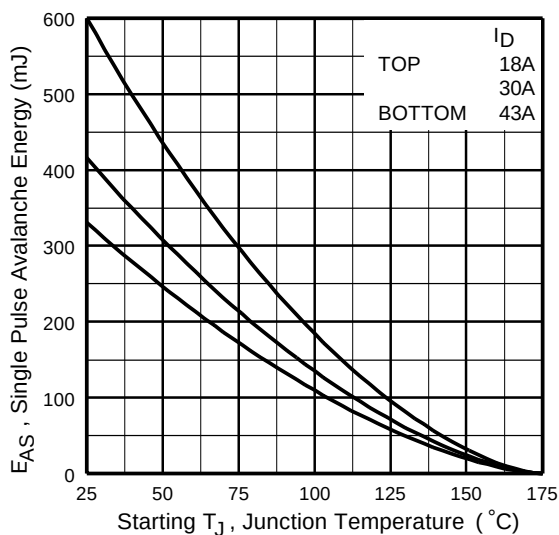


Fig 12c. Maximum Avalanche Energy
Vs. Drain Current

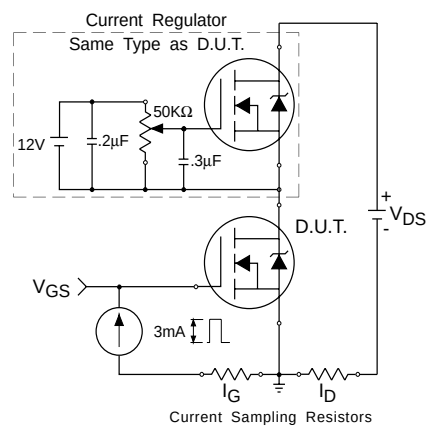
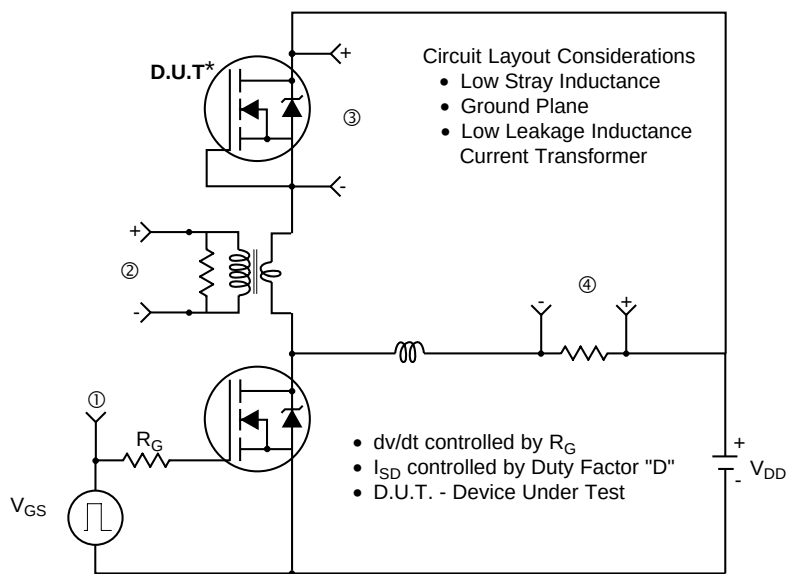


Fig 13b. Gate Charge Test Circuit

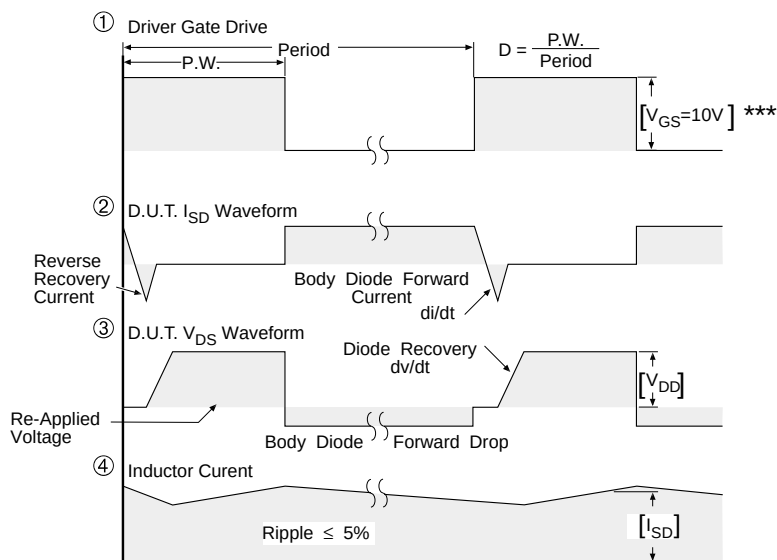
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Peak Diode Recovery dv/dt Test Circuit



* Reverse Polarity of D.U.T for P-Channel



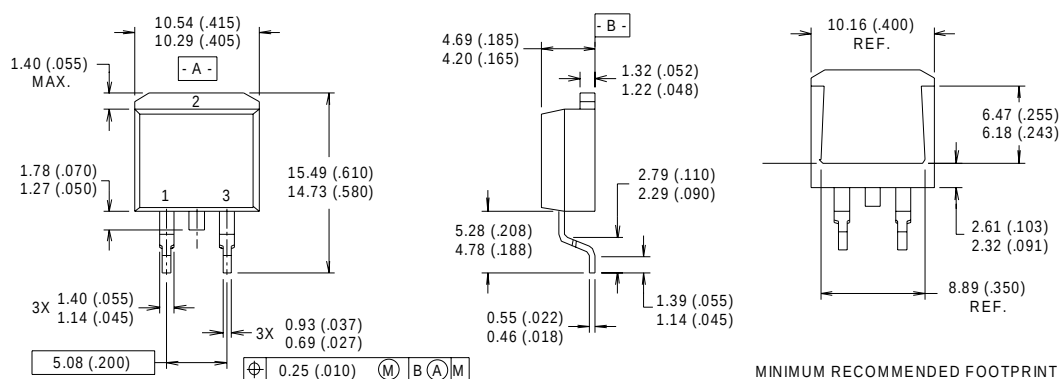
*** $V_{GS} = 5.0V$ for Logic Level and 3V Drive Devices

Fig 14. For N-channel HEXFET® power MOSFETs

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D²Pak Package Outline



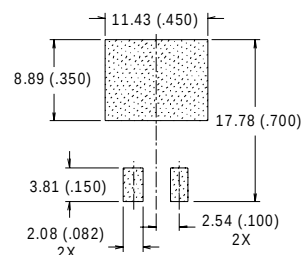
NOTES:

- 1 DIMENSIONS AFTER SOLDER DIP.
- 2 DIMENSIONING & TOLERANCING PER ANSI Y14.5M, 1982.
- 3 CONTROLLING DIMENSION : INCH.
- 4 HEATSINK & LEAD DIMENSIONS DO NOT INCLUDE BURRS.

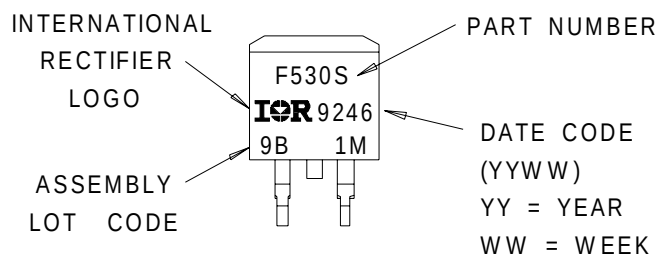
LEAD ASSIGNMENTS

- 1 - GATE
- 2 - DRAIN
- 3 - SOURCE

MINIMUM RECOMMENDED FOOTPRINT



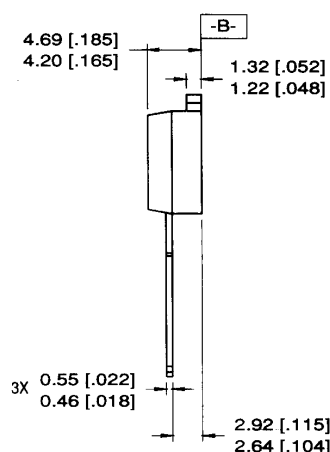
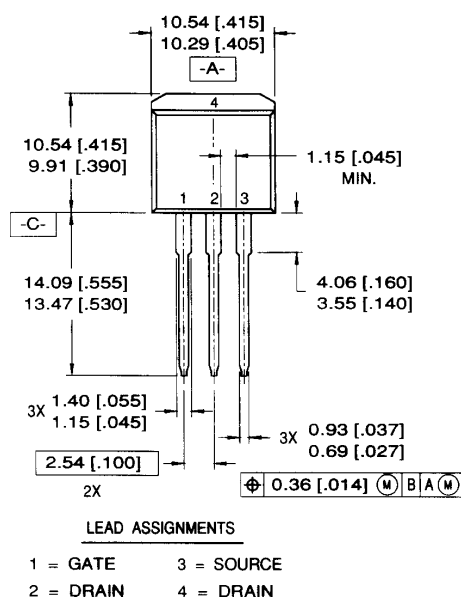
D²Pak Part Marking Information



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TO-262 Package Outline

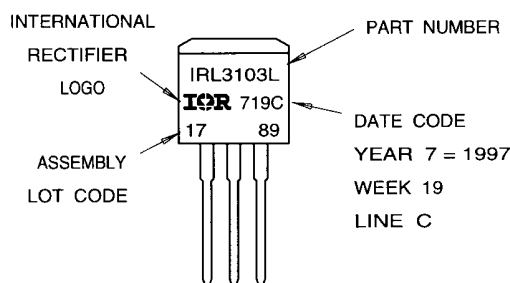


NOTES:

1. DIMENSIONING & TOLERANCING PER ANSI Y14.5M-1982
2. CONTROLLING DIMENSION: INCH.
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. HEATSINK & LEAD DIMENSIONS DO NOT INCLUDE BURRS.

TO-262 Part Marking Information

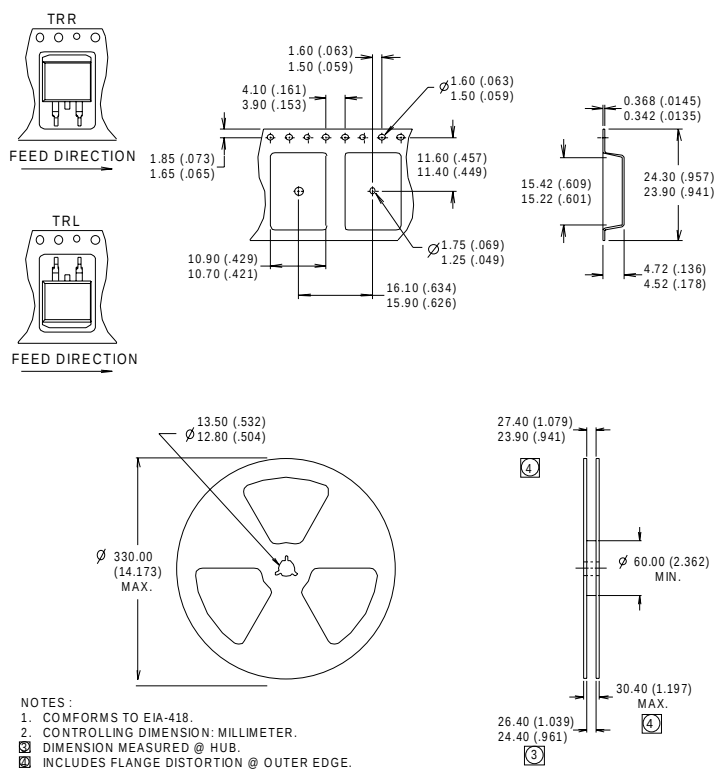
EXAMPLE: THIS IS AN IRL3103L
LOT CODE 1789
ASSEMBLED ON WW 19, 1997
IN THE ASSEMBLY LINE "C"



IRF2807S/IRF2807L

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D²Pak Tape & Reel Information



Data and specifications subject to change without notice.
This product has been designed and qualified for the Industrial market.
Qualification Standards can be found on IR's Web site.

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Note: For the most current drawings please refer to the IR website at:

<http://www.irf.com/package/>